

Références

- [1] **Patrick. Roy, Ph.D**, (1999). Etude des caractéristiques électriques de détecteurs au silicium dans les conditions d'irradiation du LHC.
- [2] **M.R.Brozel**, (1997). Irradiated Damage in GaAs particle detectors.
- [3] **B.K.Jones, J.Santana, M.Mcpherson**, (1997). Semiconductor detectors for use in high radiation damage environment-semisulating GaAs or Silicon?
- [4] **D . Zontar**, (1998). Study of radiation damage in silicon detectors for high luminosity experiments at LHC.
- [5] **Lesley J.Beattie, B.Sc(Hons)**,(1998). A macroscopic evaluation of heavily irradiated silicon diode for application in silicon detectors at LHC.
- [6] **L.J.Beattie, A.Chilingarov, T.Sloan**,(2000). Forward bias operation of SI detectors:
A way to work in high – radiation environment.
- [7] **Angela .Vasilescu**. Detectors for the study of the proton-proton interaction at very high énergie. Institute of nuclear physics and engineering. Bucharest.
- [8] **F.Hartmut, W.Sadrozinski**, (2000). Application of silicon detectors.
- [9] **D.S.McGregor, H.Hermon**, (1997). Room temperature compound semiconductor radiation detectors, Nuclear instruments and methods in physics research, A 395, pp.101-124.
- [10] **E.Vittone, F.fizzotti, A.Lo Giudice, C.paolini, C.Manfredotti**, (2000). "Theory in ion beam induced charge collection in detectors based on the extended Shckley- Ramos theorem", Nuc. Ins. Meth. Phys. Res B 161-163, 446-451.
- [11] **F.Nava, P. vanni, C.Canali, E.vittone, P.Polesselo, U.Bigger,C.Leroy**,(1999) .
Evidence for plasma effect on charge collection efficiency in proton irradiated GaAs detectors, Nuc Ins and Methods in physics research, A 426 p 185-191.
- [12] **Gerrish , Michael, McPherson**,(1997). Irradiation silicon detectors as relaxation devices, Thesis,Lancastre University.
- [13] **J.J. Mares, J.Kristofik, P.Hubik,S.Pospisil**,(1999). The role of the space charge in GaAs - Based partical detectors, Nuclear Instruments and Methods in physics

research, A 434 ,pp. 57-60.

- [14] **K.Niclas,P.Jonson**. Temperature and injection dependence of the schokley . R. H. lifetimes in electron –irradiated p-type silicon. Journal
- [15] **Wen. Lin**, (1994). Oxygen silicon, Volume 42 of semiconductors and semimetals, pp. 9-52 , Academic Pres Inc., Boston.
- [16] **Eric.Forton**, (2001). Les senseurs silicium pour CMS : Caractérisation et mise en œuvre des mesures de résistance aux rayonnements.
- [17] **B.K.Jones, M.Mc Pherson**, (1999). Radiation damaged silicon as a semi-insulating relaxation semiconductor :Static electrical properties. Semiconductor science technology .N°14, pp. 667-678 .
- [18] **Henry Mathieu**. Physique des semiconducteurs et des composants électroniques.
- [19] **S.M.Sze**. Semiconductor devices,Physics and technology.
- [20] **K.Rudolf.Bock**, (1998). Radiation damage in semiconductors.
- [21] **H . J .Queisser**, (1972). Semiconductors in relaxation regime, Solid state devices.
- [22] **L . Deihimi**, (2004). Effet des pièges sur les performances des détecteurs de particules en AsGa et silicium irradiée dans le régime de relaxation.
- [23] **M.McPherson**, (1997). Irradiated silicon detectors as relaxation devices.
- [24] **K.Zdansky, B.K.Jones, J.Santana, and T.Sloan**,(1996). Numerical analysis of charge transport in semi-insulation GaAs with two contacts, J.Appl Phys, 3611-3618.
- [25] **Hiounie .Fatima**. [2004], Simulation des caractéristiques I-V et C- V des détecteurs de Particules en Ga As.
- [26] **N.M.Heagel**,(1991). Relaxation semiconductors:In theory and in practice.Applied physics A 53, pp.1-7.
- [27] **A . Saadoun**, (2004). Calcul numérique de la capacité d'un détecteur de particules à base d'une structure p-n-n, Thèse de magistère.
- [28] **K. Zdansky**, (2000). Quasistatic capacitance – voltage characteristics of plane - parallel structures Metal-Insulator / Metal, journal of applied physics, Vol . 88 N° 4,pp.2024-2029.

- [29] **M.Mc.pherson**, (2003). The space charge relaxation behaviour of silicon diodes
Irradiation with 1Mev neutron.
- [30] **L Beattie et Al**,(1998). Forward bias I-V characteristics for heavily irradiated silicon
diode. Rose Technical, note TN /98-1.
- [31] **M.Kurata**, (1982). Numerical analysis for semiconductor devices, D.C.Heath and
Company, Canada.
- [32] **D.S.McGregor, H.Hermon**, (1997). Room temperature compound semiconductors.
nuclear Instruments and methods in physics research A 395 101-124.
- [33] **N.Croitto, P.G.Rancoita, M.Rattaggi, A.Seidman**. Influence of température on the
I- V caractéristiques of Si detectors irradiated at high fluence.
- [34] **Mara Bruzzi**, (2001). Radiation damage in silicon detectors for high energy physics
experiments.
- [35] **S.J.Watts**. Irradiation induced defects in silicon detectors.
- [36] **M.Acciari, N.Critoru, C.Leroy, A.Seidman**. Influence of high fluence neutron
Irradiation on forward current of semiconductor detectors.
- [37] **H.Ohyama, K.Takakuro and K.Hayama**, (2002). Damage coefficient in high –
temperature particle and γ -irradiated silicon p-i-n diod .
- [38] **B.K.Jones, J.Santana and M.Pherson**, (1997) . Ohmic I-V characteristics in semi-
insulating semiconductor diodes.
- [39] **S.Saramad**, (2003). A new explanation for some open questions of Hadron Irradiated
Silicon Detectors.
- [40] **W.Van Roobroeck**, (1972). Transport in relaxation semiconductors, physical review B,
Volume 5,number 6.
- [41] **H.K.Gummel**,(1964). A self–consistent iterative shema for one dimensionel steady –
state transistor calculations.
- [42] **S.Selberherr**, (1984). Analysis and simulation of semiconductor devices.
- [43] **CT.Sah, RN.Noyce, Shockley**,(1975). Proc.Ire 45, 1228.
- [44] **S. Worm** (2000). Silicon radiation damage and expected run in lifetimes .